

## PRESS RELEASE

### For Immediate Release

## **GRANDIS AWARDED NATIONAL INSTITUTE OF STANDARDS AND TECHNOLOGY (NIST) GRANT FOR NEXT-GENERATION MEMORY DEVELOPMENT**

**MILPITAS, Calif., Oct. 09, 2007** — Grandis, Inc., today announced that it has received an Advanced Technology Program (ATP) grant of US\$2 million from the U.S. Commerce Department's National Institute of Science and Technology (NIST) for use in the development of its spin-transfer torque random access memory (STT-RAM) technology. STT-RAM is a next-generation, non-volatile memory (NVM) solution designed to enable high scalability and unlimited endurance, while consuming less power than existing mainstream memories.

Yiming Huai, Ph.D., co-founder and chief technology officer of Grandis stated, "It is an honor that our STT-RAM technology has been recognized by the NIST. This generous support will significantly strengthen U.S. leadership in this critical technology and play an important role in helping us to accelerate the commercialization of STT-RAM for both the embedded and stand-alone memory markets."

As semiconductor technology scales to smaller feature sizes to support consumer demand for electronic devices with greater mobility and functionality, current mainstream semiconductor memories subsequently encounter significant performance and reliability limitations. At the same time, the integration of numerous types of volatile and non-volatile memory to support the increased functionality of these consumer products also creates numerous IC design and cost challenges. STT-RAM is a universal memory technology that addresses these challenges by enabling fast read/write capability, significantly lower power consumption and excellent scalability to future technology nodes.

Under the leadership of principal investigator, Dr. Eugene Chen, and business manager, Dr. Alexander Driskill-Smith, Grandis will leverage the NIST funding to explore several development areas—including innovations in materials, devices and circuitry. The goal of this effort is to enhance the performance of STT-RAM and enable memory devices with greater density at a lower cost per die.

The goal of the ATP program is to accelerate the development and broad dissemination of emerging or enabling technologies that can lead to revolutionary new products and services. ATP grant recipients are selected based on a rigorous, competitive peer review process, where they must meet stringent scientific and technical merit requirements, and demonstrate strong potential for broad-based economic benefits for the nation.

### **About Grandis, Inc.**

Grandis is the pioneer in the development of spin-transfer torque RAM (STT-RAM), a universal and scalable memory solution. Grandis licenses its technology to companies that are developing a variety of products incorporating stand-alone and embedded STT-RAM memory. It offers its licensees a complete range of support services from process installation through qualification. By combining non-volatility and high performance with low-power consumption and low cost, STT-RAM can revolutionize the performance of electronic products in many areas. Grandis was established in 2002, and is headquartered in Silicon Valley, California. Investors include Applied Ventures LLC, Sevin Rosen Funds, Matrix Partners, Incubic and Concept Ventures. Additional information about the company is available on the Internet at [www.grandisinc.com](http://www.grandisinc.com)

### **Contact for Grandis, Inc.**

Grandis, Inc.  
Corporate Headquarters  
1123 Cadillac Court  
Milpitas, CA 95035  
Tel +1 (408) 945-2160  
Fax +1 (408) 945-2161  
[info@grandisinc.com](mailto:info@grandisinc.com)

### **Press and Analyst Contact**

Lisa Gillette-Martin  
MCA, Inc.  
Tel +1 (650) 968-8900 x115  
[lgmartin@mcapr.com](mailto:lgmartin@mcapr.com)